

LIST OF THE CLAIMS

1. (Currently amended) A semiconductor device comprising:
a semiconductor substrate;
dummy patterns for a chemical mechanical polishing (CMP) method formed in a uniform pattern over the semiconductor substrate; and
marking patterns that are formed over the semiconductor substrate to correspond to predetermined groups of the dummy patterns ~~for counting dummy patterns~~,
wherein at least one dummy pattern is formed between two marking patterns.

2. (Original) The semiconductor device of claim 1, wherein the marking patterns have a different shape from the dummy patterns.

3. (Original) The semiconductor device of claim 1, wherein the marking patterns have a different size from the dummy patterns.

4. (Original) The semiconductor device of claim 1, wherein the marking patterns are smaller than the dummy patterns.

5-22. (Canceled)

23. (New) A semiconductor device comprising:
a semiconductor substrate;
dummy patterns for a chemical mechanical polishing (CMP) method formed in a uniform pattern over the semiconductor substrate; and
marking patterns that are formed over the semiconductor substrate to correspond

to predetermined groups of the dummy patterns,

wherein the marking patterns surround at least a group of dummy patterns.